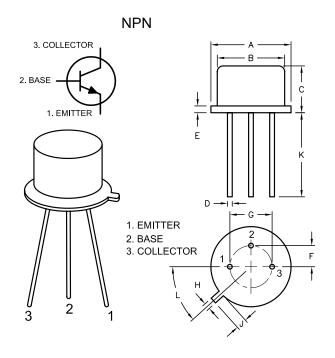


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SPC.	_F00	5.DWG

٧.	REVISIONS		DOC. NO. SPC-F005 * Effective: 7/8/02 * DCP No: 1398						
	DCP #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRVD	DATE
	1447	Α	RELEASED	HYO	5/1/02	JWM	2/20/04	JC	2/20/04
	1885	В	UPDATED TO ROHS COMPLIANCE	EO	02/03/06	НО	2/6/06	НО	2/6/06

RoHS Compliant



A B C D E F G H J

9.39 8.50 6.60 0.53 0.88 2.66 5.33 0.86 1.02

This is a silicon NPN transistor in a TO-39 type case designed primarily for amplifier and switching applications. This device features high breakdown voltage, low leakage current, low capacity, and beta useful over an extremely wide current range.

Absolute Maximum Ratings:

- Collector-Base Voltage, V_{CBO} = 120V
- Collector-Emitter Voltage, V_{CEO} = 65V
- Emitter-Base Voltage, $V_{EBO} = 7V$
- Continuous Collector Current, I_C = 1A
- Total Device Dissipation (T_A = +25°C), P_D = 800mW

Derate above 25°C = 4.6mW/°C

- Total Device Dissipation (T_C = +25°C), P_D = 5W Derate above 25°C = 28.6mW/°C

- Operating Junction Temperature Range, T_J = -65° to +200°C

- Storage Temperature Range, T_{stg} = -65° to +200°C Thermal Resistance, Junction-to-Case, R_{thJC} = 35°C/W
- Thermal Resistance, Junction-to-Ambient, R_{thJA} = 175°C/W
- Lead Temperature (During Soldering, 1/16" from case, 60sec max), T_L = 300°C

DISCLAIMER:
ALL STATEMENTS AND TECHNICAL INFORMATION CONTAINED
HEREIN ARE BASED UPON INFORMATION AND/OR TESTS WE
BELIEVE TO BE ACCURATE AND RELIABLE. SINCE
CONDITIONS OF USE ARE BEYOND OUR CONTROL, THE
USER SHALL DETERMINE THE SUITABILITY OF THE PRODUCT
FOR THE INTENDED USE AND ASSUME ALL RISK AND
LIABILITY WHATSOEVER IN CONNECTION THEREWITH.

8.50 7.74 6.09 0.40

Dimensions

Max

TOLERANCES: UNLESS OTHERWISE SPECIFIED, DIMENSIONS ARE FOR REFERENCE PURPOSES ONLY.

- |2.41 | 4.82 | 0.71 | 0.73 | 12.70 | 42°

DRAWN BY: DATE: 5/1/02 HISHAM ODISH CHECKED BY: DATE: JEFF MCVICKER 2/20/04 APPROVED BY: DATE: 2/20/04 JOHN COLE

DRAWING TITLE: Transistor, Bipolar, TO-39, Metal, NPN DWG. NO. ELECTRONIC FILE SIZE REV 2N2102 В 35C0687.DWG SCALE: NTS U.O.M.: Millimeters SHEET: 1 OF 2

Parameter	Symbol	Test Conditions	Min	Max	Unit
OFF Characteristics					
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 100mA, I _B = 0	65	-	V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	120	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = 100μA, I _C = 0	7	-	V
Collector Cut-Off Current	I _{CBO}	V _{CB} = 60V, I _E = 0	-	0.002	μΑ
Collector Cut-On Current		$V_{CB} = 60V, I_{E} = 0, T_{A} = +150^{\circ}C$	-	2	μΑ
Emitter Cut-Off Current	I _{EBO}	$V_{BE} = 5V, I_C = 0$	-	0.002	μA
ON Characteristics (Note 1)			•	•	
DC Current Gain	h _{FE}	$V_{CE} = 10V, I_{C} = 0.1mA$	20	-	-
		V _{CE} = 10V, I _C = 10mA	35	-	-
		V _{CE} = 10V, I _C = 150mA	40	120	-
		V _{CE} = 10V, I _C = 10mA, T _A = -55°C	20	-	-
		V _{CE} = 10V, I _C = 500mA	25	-	-
		V _{CE} = 10V, I _C = 1A	10	-	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 150mA, I _B = 15mA	-	0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 150mA, I _B = 15mA	-	1.1	V
Small-Signal Characteristics					
Current Gain-Bandwidth Product	f _T	V _{CF} = 10V, I _C = 50mA, f = 20MHz	60	_	MHz
Output Capacitance	C _{obo}	V _{CB} = 10V, I _E = 0, f = 1MHz	-	15	pF
Input Capacitance	C _{ibo}	V _{BE} = 500mV, I _C = 0, f = 1MHz	_	80	pF
Small-Signal Current Gain	h _{fe}	$V_{CE} = 5V$, $I_{C} = 1$ mA, $f = 1$ kHz	30	100	<u> -</u>
Noise Figure	NF	$V_{CE} = 10V, I_{C} = 100\mu A, f = 1kHz, R_{S} = 1kohm$	-	6	dB

SIZE

Α

SCALE: NTS

DWG. NO.

2N2102

U.O.M.: Millimeters

ELECTRONIC FILE

35C0687.DWG

SHEET:

REV

В

2 OF 2

SPC-F005.DWG

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